Ordering number : EN2007C

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA1419/2SC3649 — High-Voltage Switching Applications

PNP / NPN Epitaxial Planar Silicon Transistor

Features

- Adoption of FBET, MBIT processes
- High breakdown voltage and large current capacity
- Ultrasmall size making it easy to provide high-density, small-sized hybrid IC's

Specifications ( ) : 2SA1419

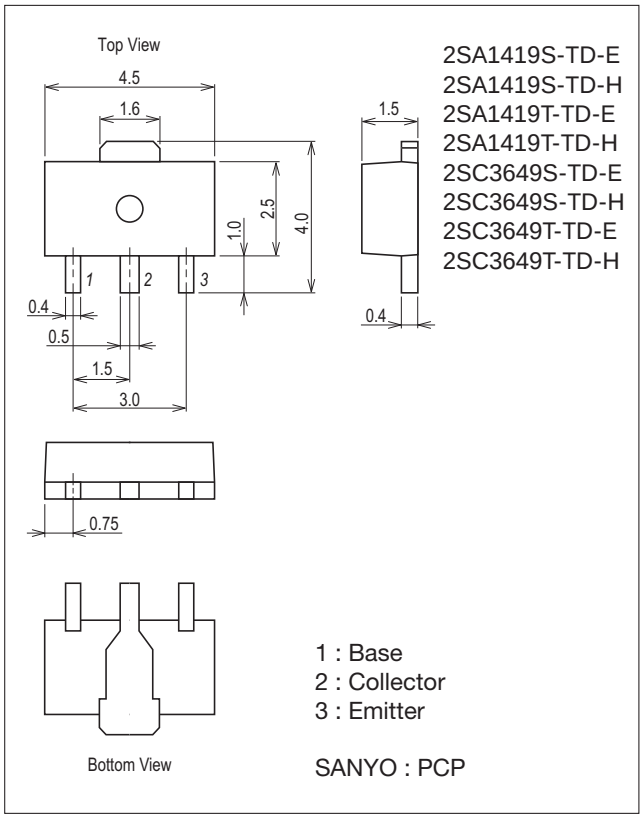
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(–)180	V
Collector-to-Emitter Voltage	V_{CEO}		(–)160	V
Emitter-to-Base Voltage	V_{EBO}		(–)6	V
Collector Current	I_C		(–)1.5	A
Collector Current (Pulse)	I_{CP}		(–)2.5	A
Collector Dissipation	P_C		500	mW
		When mounted on ceramic substrate (250mm^2×0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Package Dimensions

unit : mm (typ)

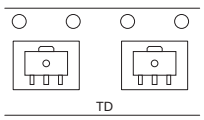
7007B-004



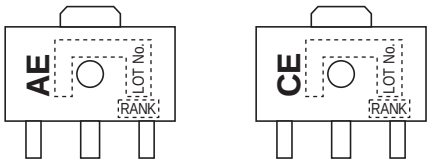
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

Packing Type: TD

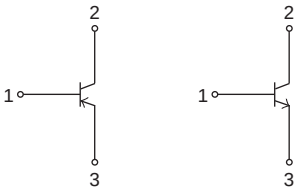


Marking



2SA1419 2SC3649

Electrical Connection



2SA1419 2SC3649

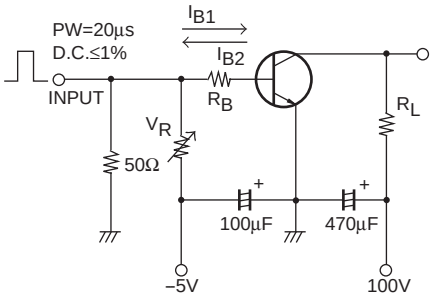
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(−)120V, I_E=0A			(−)1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(−)4V, I_C=0A			(−)1	μA
DC Current Gain	$h_{FE}1$	V_{CE}=(−)5V, I_C=(−)100mA	100*		400*	
	$h_{FE}2$	V_{CE}=(−)5V, I_C=(−)10mA	80			
Gain-Bandwidth Product	f_T	V_{CE}=(−)10V, I_C=(−)50mA		120		MHz
Output Capacitance	Cob	V_{CB}=(−)10V, f=1MHz		(22)14		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=(−)500mA, I_B=(−)50mA		(−200)130	(−500)450	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=(−)500mA, I_B=(−)50mA		(−)0.85	(−)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(−)10μA, I_E=0A	(−)180			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(−)1mA, R_{BE}=∞	(−)160			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(−)10μA, I_C=0A	(−)6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		(40)40		ns
Storage Time	t_{stg}			(0.7)1.2		μs
Fall Time	t_f			(40)80		ns

* : The 2SA1419 / 2SC3649 are classified by 100mA h_{FE} as follows :

Rank	R	S	T
h_{FE}	100 to 200	140 to 280	200 to 400

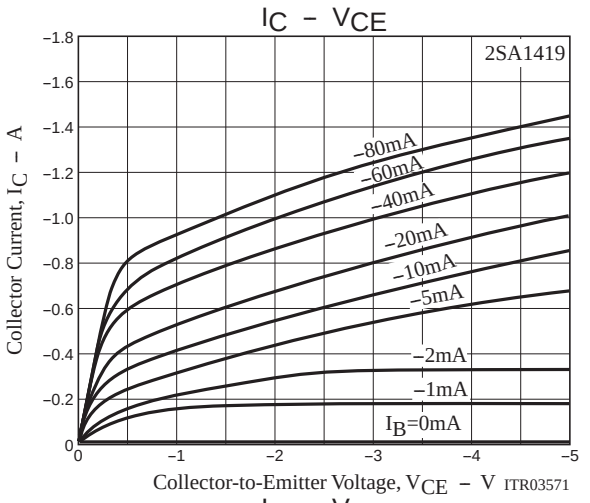
Switching Time Test Circuit

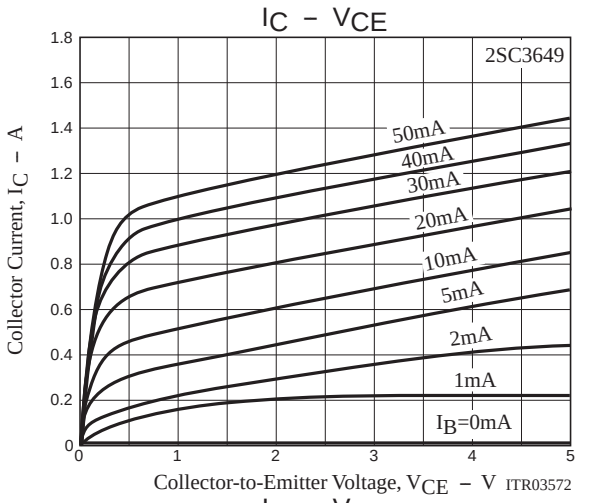


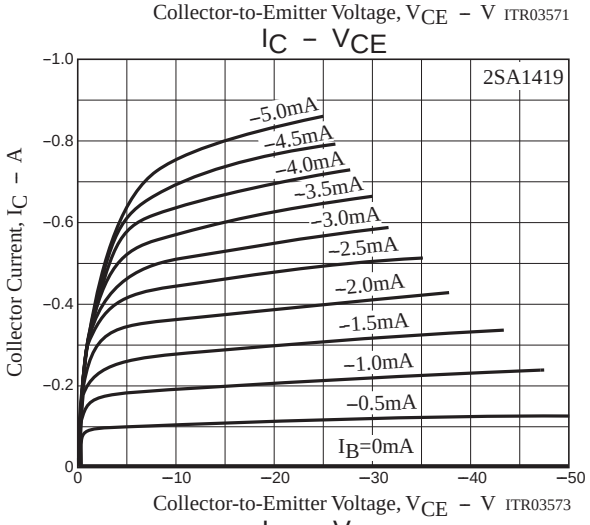
I_C=10I_{B1}=−10I_{B2}=0.7A
(For PNP, the polarity is reversed)

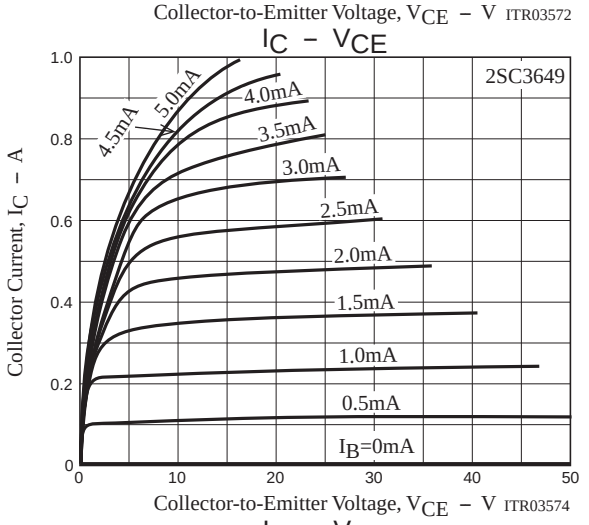
Ordering Information

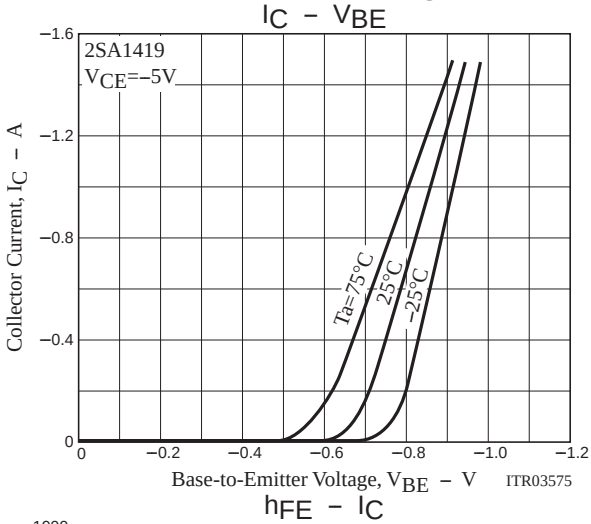
Device	Package	Shipping	memo
2SA1419S-TD-E	PCP	1,000pcs./reel	Pb Free
2SA1419S-TD-H	PCP	1,000pcs./reel	Pb Free and Halogen Free
2SA1419T-TD-E	PCP	1,000pcs./reel	Pb Free
2SA1419T-TD-H	PCP	1,000pcs./reel	Pb Free and Halogen Free
2SC3649S-TD-E	PCP	1,000pcs./reel	Pb Free
2SC3649S-TD-H	PCP	1,000pcs./reel	Pb Free and Halogen Free
2SC3649T-TD-E	PCP	1,000pcs./reel	Pb Free
2SC3649T-TD-H	PCP	1,000pcs./reel	Pb Free and Halogen Free

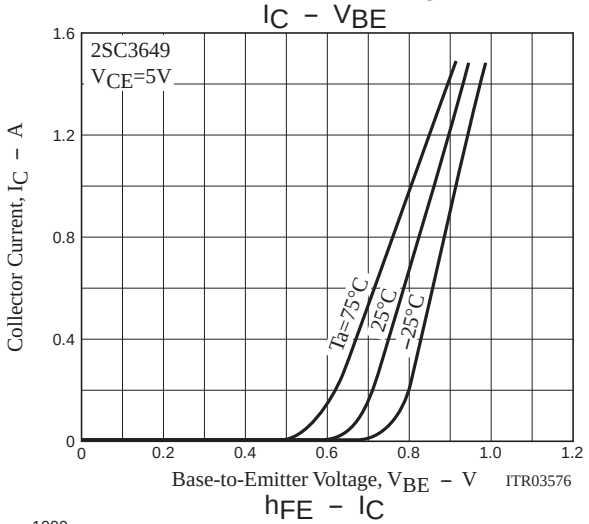

IC – VCE
2SA1419
Collector Current, IC – A
–80mA
–60mA
–40mA
–20mA
–10mA
–5mA
–2mA
–1mA
IB=0mA
Collector-to-Emitter Voltage, VCE – V
ITR03571

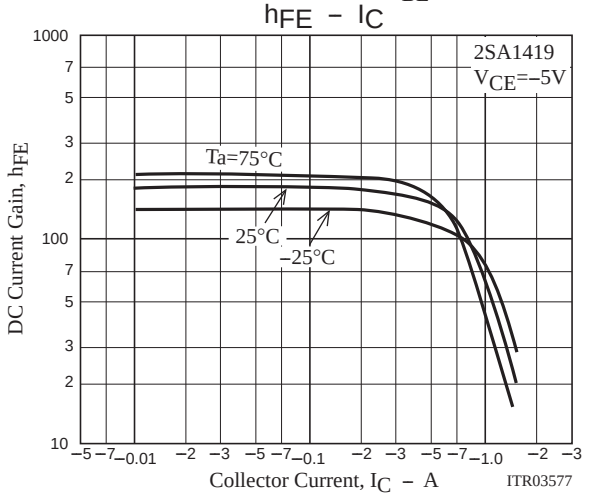

IC – VCE
2SC3649
Collector Current, IC – A
50mA
40mA
30mA
20mA
10mA
5mA
2mA
1mA
IB=0mA
Collector-to-Emitter Voltage, VCE – V
ITR03572

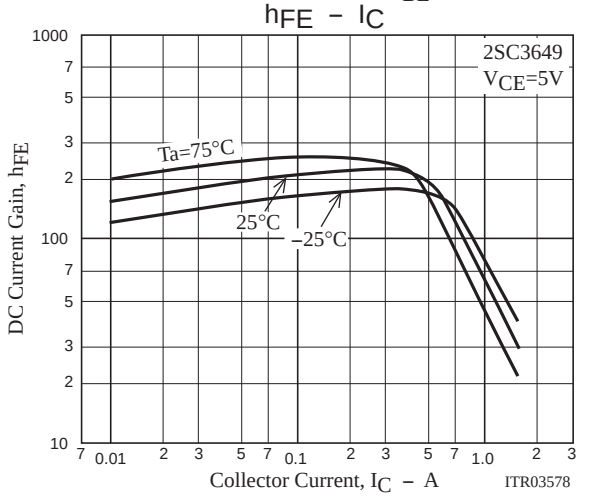

IC – VCE
2SA1419
Collector Current, IC – A
–5.0mA
–4.5mA
–4.0mA
–3.5mA
–3.0mA
–2.5mA
–2.0mA
–1.5mA
–1.0mA
–0.5mA
IB=0mA
Collector-to-Emitter Voltage, VCE – V
ITR03573

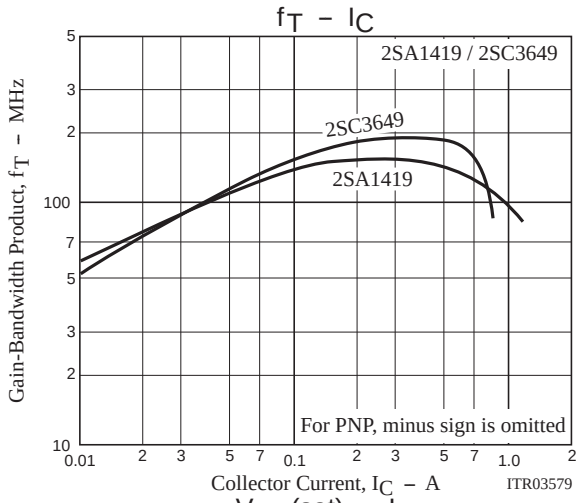

IC – VCE
2SC3649
Collector Current, IC – A
4.5mA
5.0mA
4.0mA
3.5mA
3.0mA
2.5mA
2.0mA
1.5mA
1.0mA
0.5mA
IB=0mA
Collector-to-Emitter Voltage, VCE – V
ITR03574

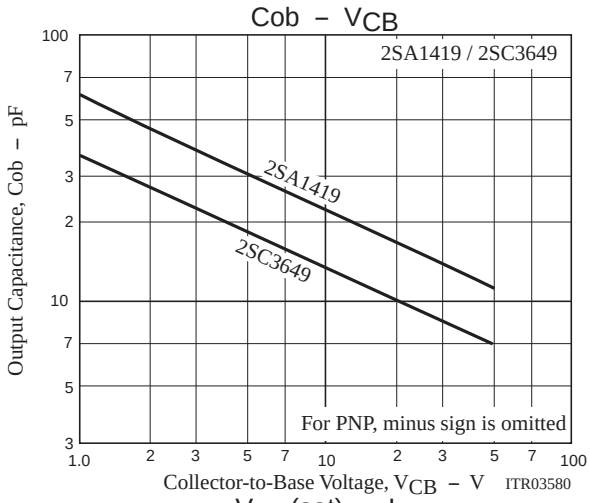

IC – VBE
2SA1419
VCE=–5V
Collector Current, IC – A
Ta=75°C
25°C
–25°C
Base-to-Emitter Voltage, VBE – V
ITR03575

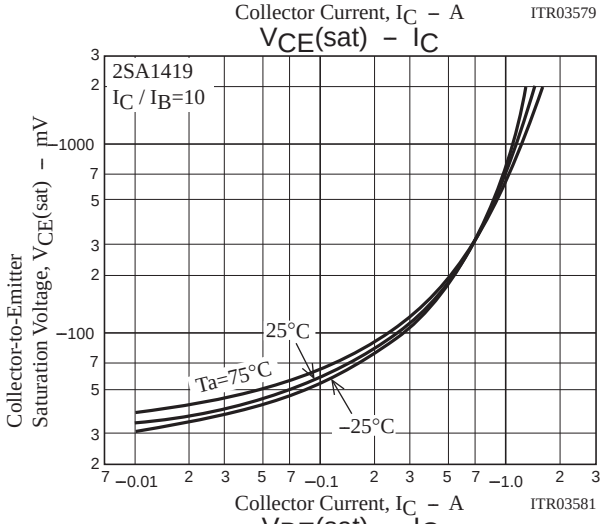

IC – VBE
2SC3649
VCE=5V
Collector Current, IC – A
Ta=75°C
25°C
–25°C
Base-to-Emitter Voltage, VBE – V
ITR03576

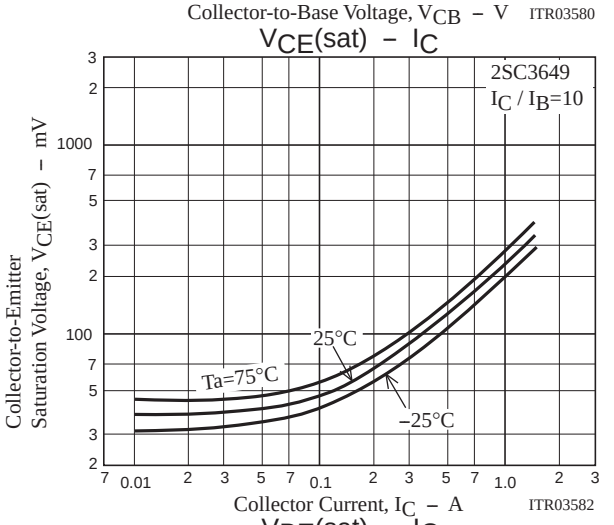

hFE – IC
2SA1419
VCE=–5V
DC Current Gain, hFE
Ta=75°C
25°C
–25°C
Collector Current, IC – A
ITR03577

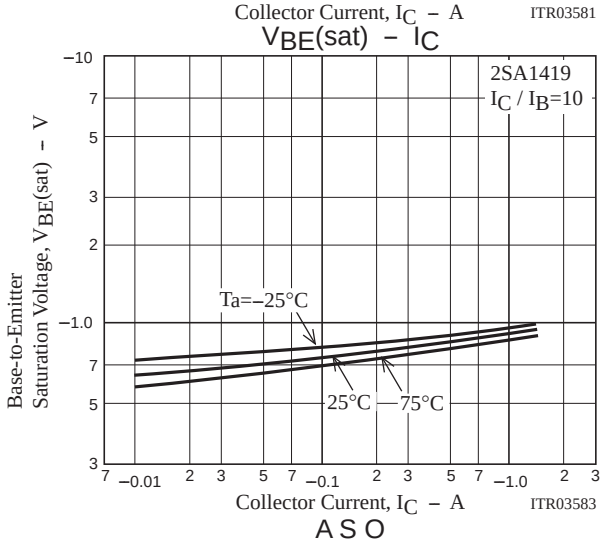

hFE – IC
2SC3649
VCE=5V
DC Current Gain, hFE
Ta=75°C
25°C
–25°C
Collector Current, IC – A
ITR03578

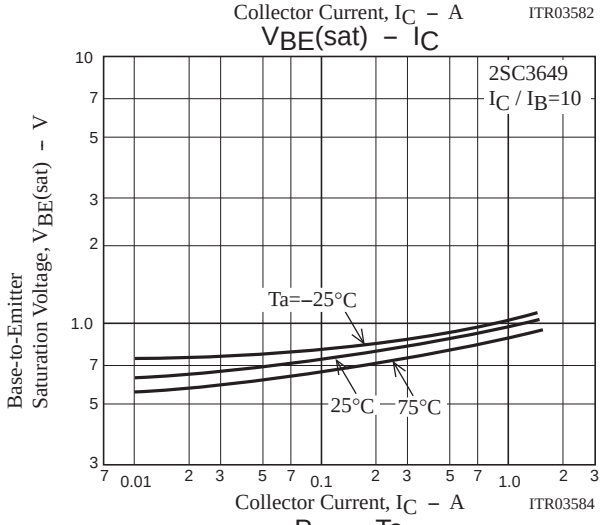

fT – IC
2SA1419 / 2SC3649
2SC3649
2SA1419
For PNP, minus sign is omitted
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
ITR03579

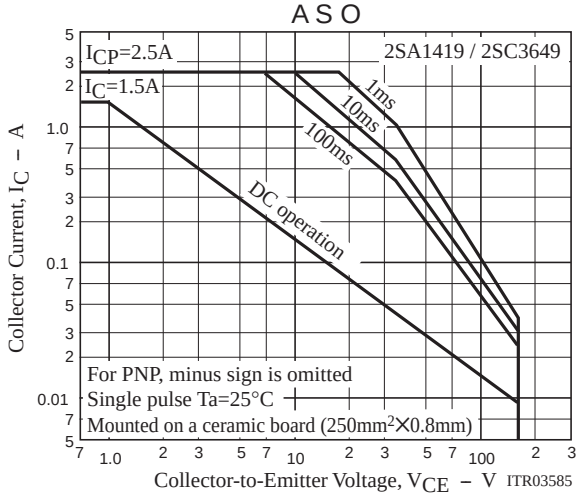

Cob – VCB
2SA1419 / 2SC3649
2SA1419
2SC3649
For PNP, minus sign is omitted
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
ITR03580

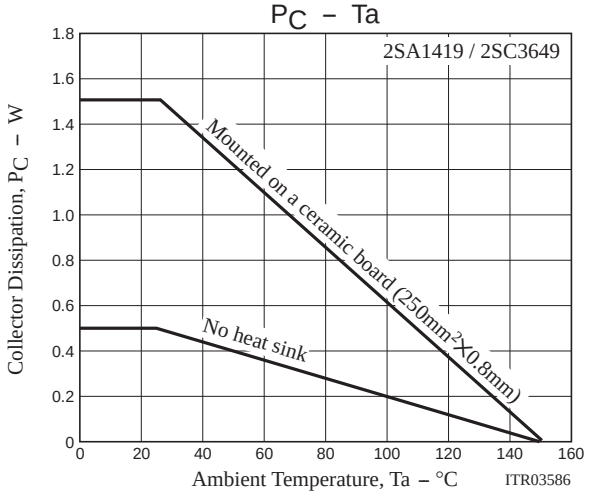

VCE(sat) – IC
2SA1419
IC / IB=10
25°C
Ta=75°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – mV
Collector Current, IC – A
ITR03581


VCE(sat) – IC
2SC3649
IC / IB=10
25°C
Ta=75°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – mV
Collector Current, IC – A
ITR03582


VBE(sat) – IC
2SA1419
IC / IB=10
Ta=–25°C
25°C
75°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
ITR03583


VBE(sat) – IC
2SC3649
IC / IB=10
Ta=–25°C
25°C
75°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
ITR03584


A S O
ICP=2.5A
IC=1.5A
2SA1419 / 2SC3649
1ms
10ms
100ms
DC operation
For PNP, minus sign is omitted
Single pulse Ta=25°C
Mounted on a ceramic board (250mm²×0.8mm)
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
ITR03585


PC – Ta
2SA1419 / 2SC3649
Mounted on a ceramic board (250mm²×0.8mm)
No heat sink
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
ITR03586

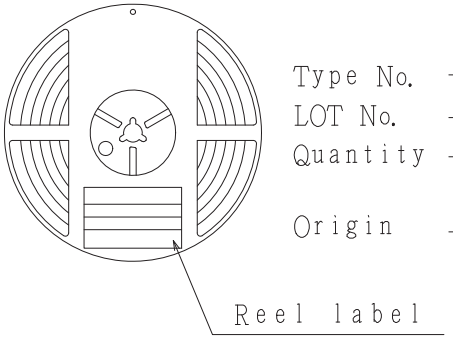
Bag Packing Specification

2SA1419S-TD-E, 2SA1419S-TD-H, 2SA1419T-TD-E, 2SA1419T-TD-H, 2SC3649S-TD-E, 2SC3649S-TD-H, 2SC3649T-TD-E, 2SC3649T-TD-H

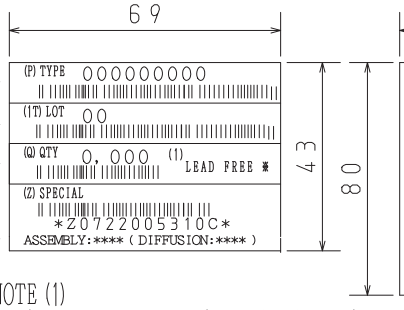
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
PCP	PCP	1,000	4,000	24,000	4 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method

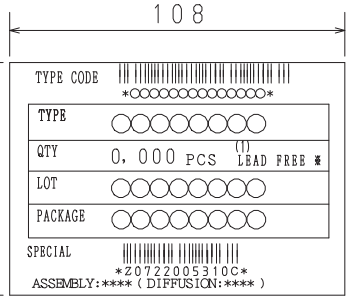


Reel label, Inner box label (unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.

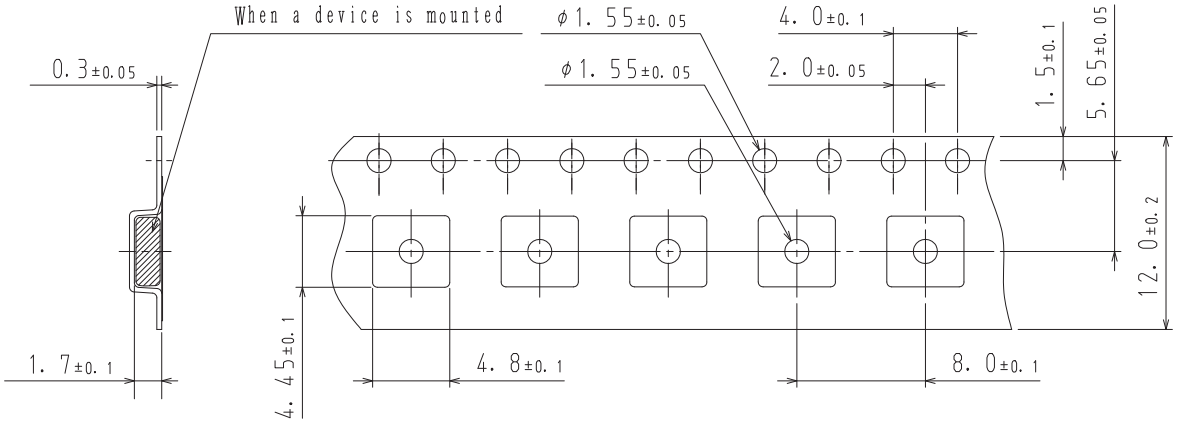


NOTE (1)
The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

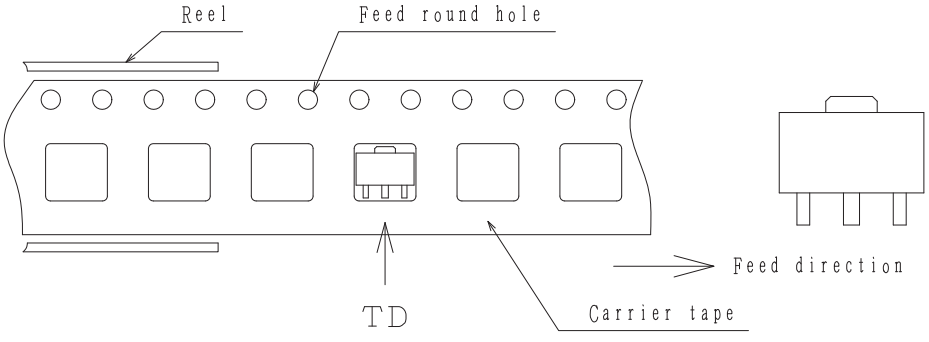
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

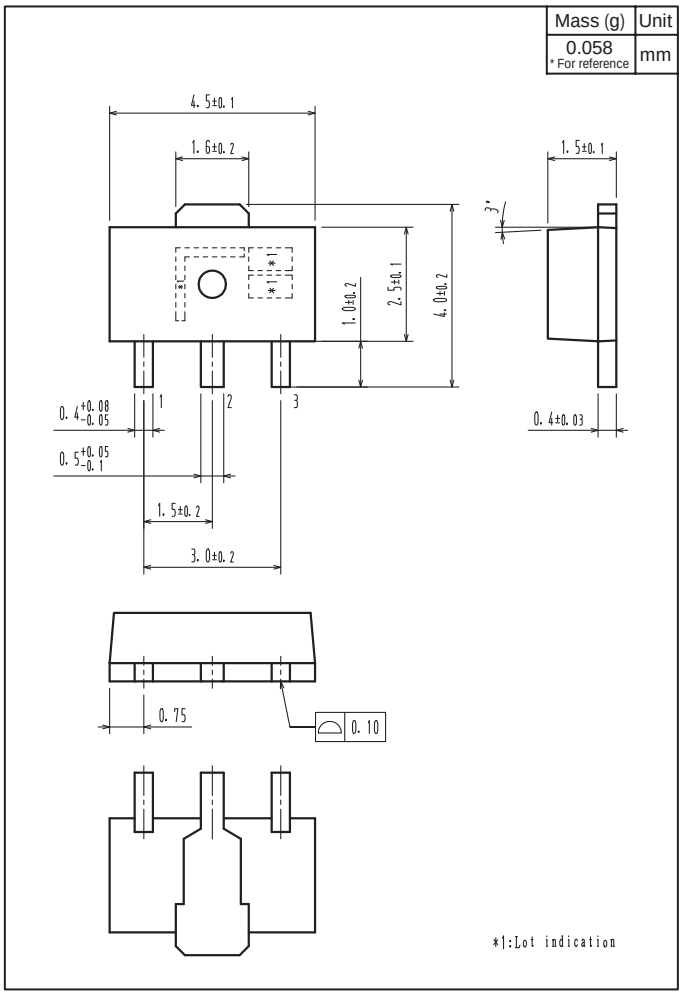


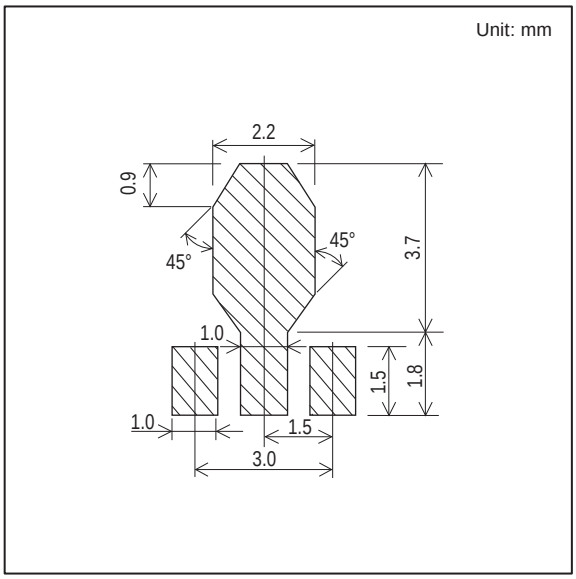
Those with pin 1 index on the feed hole side·····TD

Outline Drawing

Land Pattern Example

2SA1419S-TD-E, 2SA1419S-TD-H, 2SA1419T-TD-E, 2SA1419T-TD-H, 2SC3649S-TD-E, 2SC3649S-TD-H, 2SC3649T-TD-E, 2SC3649T-TD-H





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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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